Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	19	'Murata' and 'Renesas'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 09:09
L3	144	'nakamura' and 'Renesas'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 09:11
L4	294	'suzuki' and 'Renesas'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 09:11
L5	36	'suzuki' and 'Renesas' and 'vertical'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 09:11
L6	43	'suzuki' and 'Renesas' and 'SRAM'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 09:11
L7	22	'nakamura' and 'Renesas' and 'SRAM'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 09:11
L11	88	@ad<="20040114" and 'vertical MISFET'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 11:25
L13	686	@ad<="20040114" and 'SRAM' and 'MISFET'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 11:16
L14	1	"5936280".PN.	USPAT; USOCR	OR	ON	2005/10/04 10:11
L15	264	@ad<="20040114" and 'SRAM' and 'MISFET' and 'dielectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 11:08
L16	2	("6483136").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/04 10:39

L17	1	"5472893".PN.	USPAT; USOCR	OR	ON	2005/10/04 10:41
L18	0	@ad<="20040114" and 'SRAM' and 'vertical' with 'FET' and 'first dielectric' and 'second dielectric' and 'third dielectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 11:09
L19	7	@ad<="20040114" and 'vertical' with 'FET' and 'first dielectric' and 'second dielectric' and 'third dielectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 11:10
L20	171	@ad<="20040114" and 'vertical' with 'conductive' and 'first dielectric' and 'second dielectric' and 'third dielectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 11:10
L21	0	@ad<="20040114" and 'MISFET' and 'conductive side wall' and 'first dielectric' and 'second dielectric' and 'third dielectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 16:11
L22	2	@ad<="20040114" and 'MISFET' and 'conductive side wall' and 'dielectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 11:11
L24	6	@ad<="20040114" and 'MISFET' and 'conductive sidewall'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 11:17
L25	111	@ad<="20040114" and 'columnar' and 'conductive' with 'side wall'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 11:18
L26	273	@ad<="20040114" and 'columnar' and 'conductive' with ('side wall' or 'sidewall')	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 11:35
L27	2237	@ad<="20040114" and 'vertical' with 'FET'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 11:38
L28	18	@ad<="20040114" and 'columnar' and 'conductive' with ('side wall' or 'sidewall') and 'RAM'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 11:35
L29	627	@ad<="20040114" and 'vertical' with 'FET' and 'memory'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 11:38

L30	99	@ad<="20040114" and (438/222). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 11:43
L31	83	@ad<="20040114" and (438/206). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 11:43
L37	0	'masaru hisamoto' and 'hitachi'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 13:23
L38	136	'hisamoto' and 'hitachi'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 13:23
L39	114	@ad<="20040114" and 'MISFET' and 'dielectric' same 'cvd' same 'temperature'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:07
L42	0	@ad<="20040114" and 'silicon nitride' same 'depostition' same 'cvd' same 'temperature'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:08
L44	448	@ad<="20040114" and 'silicon nitride' with 'deposition' same 'cvd' with 'temperature'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:09
L45	246	@ad<="20040114" and 'silicon nitride' with 'deposition' with 'cvd' with 'temperature'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:09
L46	165	'TEOS' same 'CVD' with 'tetraethoxysilane' same 'silicon nitride'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:52
L47	53	'TEOS' same 'CVD' with 'tetraethoxysilane' with 'silicon nitride'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:52
L48	53	'TEOS' with 'CVD' with 'tetraethoxysilane' with 'silicon nitride'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:12

L50	106	'silicon nitride' with 'silicon oxide' with 'Cvd' same 'tetraethoxysilane'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:00
L51	441	@ad<="20040114" and 'TEOS' with 'silicon oxide' with 'CVD' with 'tetraethoxysilane'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:15
L52	184	@ad<="20040114" and 'TEOS' with 'silicon oxide' with 'CVD' with 'tetraethoxysilane' and 'ozone' and 'temperature'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:15
L53	27	@ad<="20040114" and 'TEOS' with 'silicon oxide' with 'CVD' with 'tetraethoxysilane' same 'ozone' same 'temperature'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:41
L54	4	@ad<="20040114" and 'TEOS' with 'silicon oxide' with 'CVD' with 'tetraethoxysilane' same 'ozone' same 'plasma' with 'density'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:47
L55	0	@ad<="20040114" and 'silicon oxide' with 'CVD' with 'tetraethoxysilane' same 'plasma density' with '10'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:45
L56	0	@ad<="20040114" and 'silicon oxide' with 'CVD' same 'plasma density' with '10'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:45
L57	24	@ad<="20040114" and 'silicon oxide' with 'CVD' same 'plasma density'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:48
L58	23	@ad<="20040114" and 'silicon oxide' with 'CVD' same 'plasma density' and '10'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:49
L59	3	@ad<="20040114" and 'silicon oxide' with 'CVD' same 'plasma density' and '"10.sup.11"'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:51
L60	4	@ad<="20040114" and 'silicon oxide' same 'CVD' same 'plasma density' and '"10.sup.11"'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:51

L62	422	@ad<="20040114" and 'MISFET' and 'hitachi' and 'SRAM'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 16:16
L63	0	@ad<="20040114" and 'MISFET' and 'hitachi' and 'SRAM' and 'eliptical'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 16:16
L64	0	@ad<="20040114" and 'MISFET' and 'SRAM' and 'eliptical'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 16:17
L65	2	@ad<="20040114" and 'MISFET' and 'hitachi' and 'SRAM' and 'elliptical'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 16:16
L66	7	@ad<="20040114" and 'MISFET' and 'SRAM' and 'elliptical'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 16:17
S1	8	(("5198683") or ("5670803") or ("5994735") or ("5627390")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/05 14:06
S2	2	"20040140502"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 11:51
S3	208	suzuki-yasumichi.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 14:06
S4	5	suzuki-yasumichi.in. and 'SRAM'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 14:12
S5	2	suzuki-yasumichi.in. and 'MISFET'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 14:08
S6	252	@ad<="20040114" and 'vertical' with 'MISFET'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 14:11

S7	864	(257/328).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 14:09
S8	826	@ad<="20040114" and (257/903). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 13:22
S9	238	@ad<="20040114" and (257/322). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 14:10
S10	785	@ad<="20040114" and (257/e21. 661).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 14:10
S11	634	@ad<="20040114" and (257/e27. 098).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 14:10
S12	214	@ad<="20040114" and (438/212). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 11:43
S13	630	@ad<="20040114" and (438/268). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 14:11
S14	1036	@ad<="20040114" and (438/197). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 14:11
S15	55	@ad<="20040114" and (438/198). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 14:11
S16	194	@ad<="20040114" and 'vertical' and 'MISFET' and 'SRAM'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 10:07
S17	107	IWAI-HIDETOSHI.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 15:34

S18	18	IWAI-HIDETOSHI.in. and 'SRAM'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 14:12
S19	34	IWAI-HIDETOSHI.in. and 'mask'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 15:34
S20	156	@ad<="20040114" and 'vertical' and 'MISFET' and 'SRAM' and 'mask'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:06